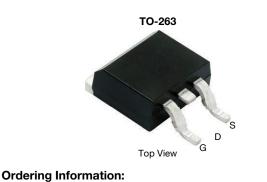
SUM120N04-1m7L

Vishay Siliconix



N-Channel 40 V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	R_{DS(on)} (Ω) MAX.	I _D (A) ^d	Q _g (TYP.)			
40	0.0017 at V _{GS} = 10 V	120	190			
40	0.0020 at V _{GS} = 4.5 V	120	190			



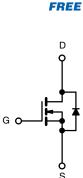
SUM120N04-1m7L-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

- TrenchFET® power MOSFET
- 100 % R_g and UIS tested
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- Power supply
 Secondary synchronous rectification
- DC/DC converter
- Power tools
- Motor drive switch



RoHS COMPLIANT

HALOGEN

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-Source Voltage	V _{DS}	40	V			
Gate-Source Voltage	V _{GS}	± 20	V			
Continuous Drain Current (T. 150 °C)	T _C = 25 °C		120 ^d			
Continuous Drain Current ($T_J = 150 \ ^{\circ}C$)	T _C = 70 °C	I _D	120 ^d	_		
Pulsed Drain Current (t = 100 µs)	I _{DM}	480	- A			
Avalanche Current	I _{AS}	92	1			
Single Avalanche Energy ^a	L = 0.1 mH	E _{AS}	423	mJ		
Maximum Dawar Dissinction 3	T _C = 25 °C	P	375 ^b	w		
Maximum Power Dissipation ^a	T _C = 25 °C ^c	– P _D –	125 ^b	vv		
Operating Junction and Storage Temperature Ra	ange	T _J , T _{stg}	-55 to +175	°C		

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	LIMIT	UNIT		
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	40	°C/W		
Junction-to-Case (Drain)	R _{thJC}	0.4			

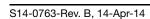
Notes

a. Duty cycle \leq 1 %.

b. See SOA curve for voltage derating.

c. When mounted on 1" square PCB (FR-4 material).

d. Package limited.



SUM120N04-1m7L



Vishay Siliconix

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static			•				
Drain-Source Breakdown Voltage	V _{DS}	V_{DS} $V_{GS} = 0 V, I_D = 250 \mu A$		-	-	V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	1.5	-	2.5	v	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$	-	-	± 250	nA	
		$V_{DS} = 40 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	-	-	1	μA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 40 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 125 ^{\circ}\text{C}$	-	-	150		
		$V_{DS} = 40 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$	-	-	5	mA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	120	-	-	А	
Drain Source On State Desistance a	Б	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 30 \text{ A}$	-	0.0014	0.0017	0	
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 20 \text{ A}$	-	0.0015	0.0020	Ω	
Forward Transconductance ^a	g _{fs}	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 20 \text{ A}$	-	212	-	S	
Dynamic ^b			•				
Input Capacitance	C _{iss}		-	11 685	-	pF	
Output Capacitance	Coss	$V_{GS} = 0 V$, $V_{DS} = 20 V$, f = 1 MHz	-	1652	-		
Reverse Transfer Capacitance	C _{rss}		-	733	-		
Total Gate Charge ^c	Qg		-	190	285		
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 20 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$	-	29	-	nC	
Gate-Drain Charge ^c	Q _{gd}		-	27	-	Ì	
Gate Resistance	Rg	f = 1 MHz	0.2	1.07	2.14	Ω	
Turn-On Delay Time ^c	t _{d(on)}		-	15	23		
Rise Time ^c	t _r	$V_{DD} = 20 \text{ V}, \text{ R}_{L} = 2 \Omega$	-	10	20	ns	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong$ 10 A, V_{GEN} = 10 V, R_g = 1 Ω	-	74	111		
Fall Time ^c	t _f		-	12	20		
Drain-Source Body Diode Ratings an	d Characteris	stics ^b (T _C = 25 °C)		·			
Pulsed Current	I _{SM}		-	-	480	А	
Forward Voltage ^a	V _{SD}	$I_{F} = 10 \text{ A}, V_{GS} = 0 \text{ V}$	-	0.8	1.5	V	

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

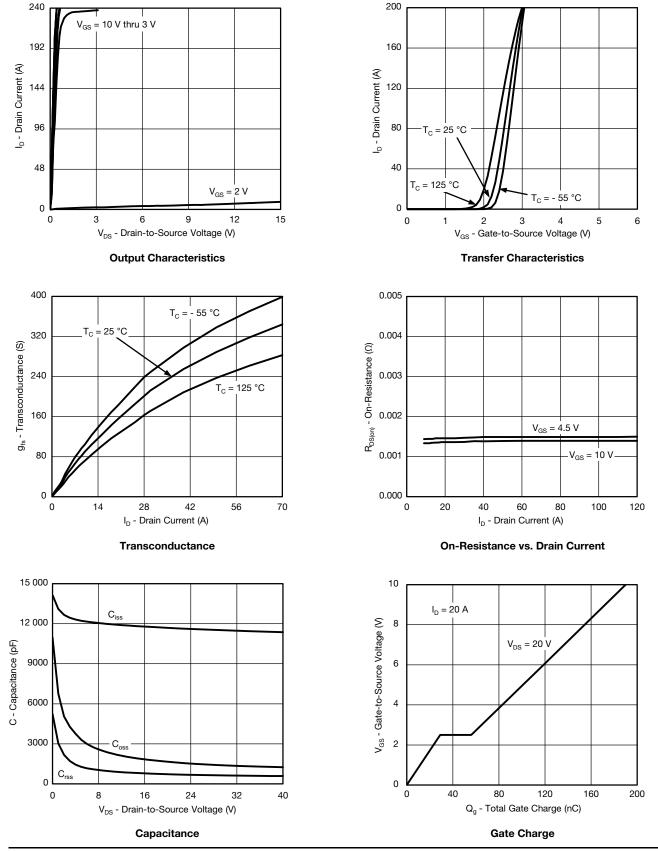
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



SUM120N04-1m7L

Vishay Siliconix

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



S14-0763-Rev. B, 14-Apr-14

3

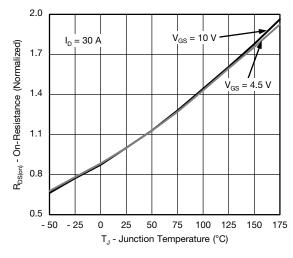
Document Number: 62920

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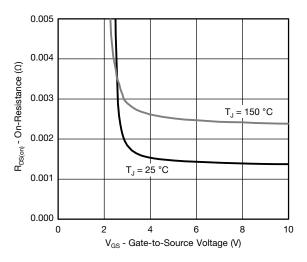


Vishay Siliconix

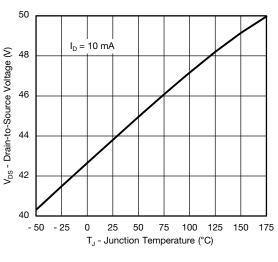
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



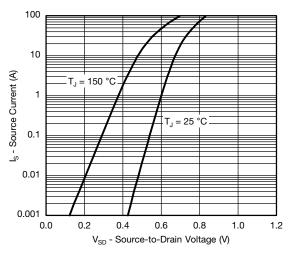
On-Resistance vs. Junction Temperature



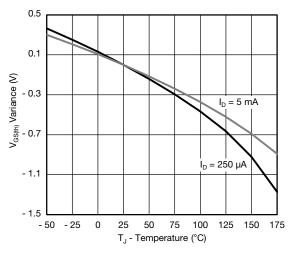
On-Resistance vs. Gate-to-Source Voltage



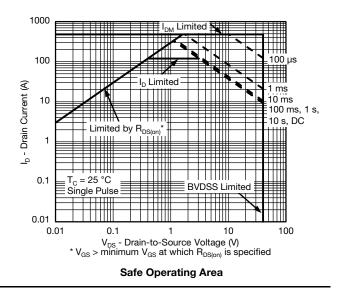
Drain Source Breakdown vs. Junction Temperature



Source-Drain Diode Forward Voltage



Threshold Voltage



S14-0763-Rev. B, 14-Apr-14

4

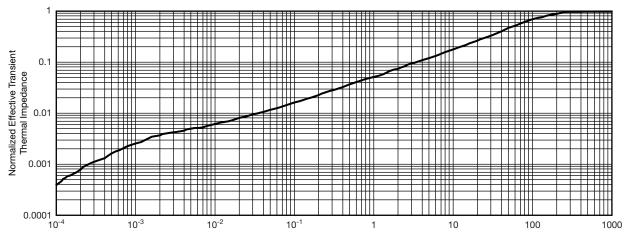
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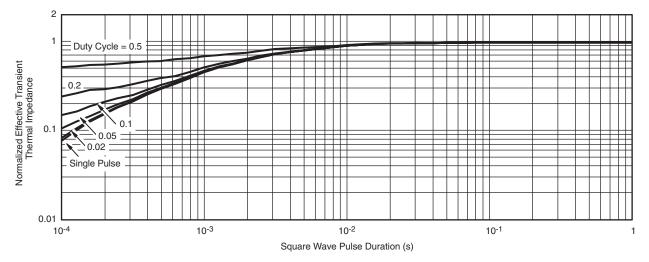
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Square Wave Pulse Duration (s)

Normalized Thermal Transient Impedance, Junction-to-Ambient





Note

• The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

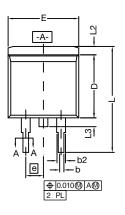
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

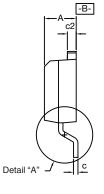
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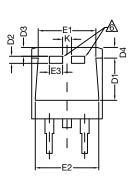


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TO-263 (D²PAK): 3-LEAD

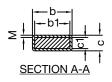








DETAIL A (ROTATED 90°)



		INCHES		MILLIMETERS		
DIM.		MIN.	MAX.	MIN.	MAX.	
А		0.160	0.190	4.064	4.826	
b		0.020	0.039	0.508	0.990	
	b1	0.020	0.035	0.508	0.889	
	b2	0.045	0.055	1.143	1.397	
с*	Thin lead	0.013	0.018	0.330	0.457	
C	Thick lead	0.023	0.028	0.584	0.711	
c1	Thin lead	0.013	0.017	0.330	0.431	
CI	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
	D	0.340	0.380	8.636	9.652	
	D1	0.220	0.240	5.588	6.096	
D2		0.038	0.042	0.965	1.067	
D3		0.045	0.055	1.143	1.397	
D4		0.044	0.052	1.118	1.321	
	E	0.380	0.410	9.652	10.414	
	E1	0.245	-	6.223	-	
	E2	0.355	0.375	9.017	9.525	
	E3	0.072	0.078	1.829	1.981	
	е	0.100	BSC	2.54	BSC	
	К	0.045	0.055	1.143	1.397	
	L	0.575	0.625	14.605	15.875	
L1		0.090	0.110	2.286	2.794	
L2		0.040	0.055	1.016	1.397	
L3		0.050	0.070	1.270	1.778	
	L4	0.010 BSC		0.254 BSC		
	М	-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13 DWG: 5843						

Notes

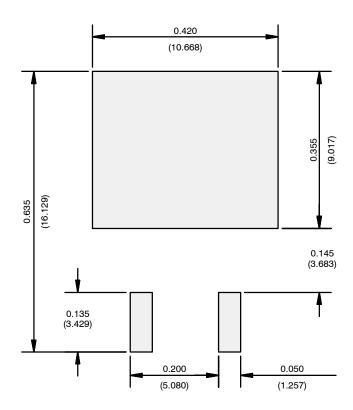
- 1. Plane B includes maximum features of heat sink tab and plastic. 2. No more than 25 $\,\%\,$ of L1 can fall above seating plane by
- max. 8 mils. 3. Pin-to-pin coplanarity max. 4 mils.
- 4. *: Thin lead is for SUB, SYB.
 - Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

This feature is for thick lead.

Revison: 30-Sep-13



RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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